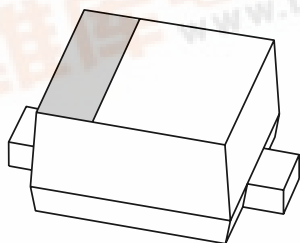


## DISCRETE SEMICONDUCTORS

# DATA SHEET



## PMEG2005EB

Low  $V_F$  MEGA Schottky barrier diode

Product specification  
Supersedes data of 2003 Feb 20

2003 Apr 04

Low  $V_F$  MEGA Schottky barrier diode

## PMEG2005EB

## FEATURES

- Forward current: 0.5 A
- Reverse voltage: 20 V
- Very low forward voltage
- Guard ring protected
- Ultra small SMD package.

## APPLICATIONS

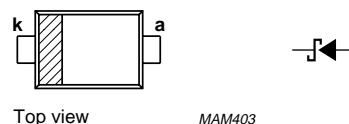
- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Low current rectification
- Low power consumption applications (e.g. handheld devices).

## DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode, encapsulated in a SOD523 (SC-79) ultra small SMD plastic package.

## PINNING

PIN	DESCRIPTION
1	cathode
2	anode



**Marking code:** L5.

The marking bar indicates the cathode.

Fig.1 Simplified outline (SOD523; SC-79) and symbol.

## LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_R$	continuous reverse voltage		–	20	V
$I_F$	continuous forward current		–	500	mA
$I_{FRM}$	repetitive peak forward current	$t_p = 1 \text{ ms}$ ; $\delta \leq 0.25$	–	3.5	A
$I_{FSM}$	non-repetitive peak forward current	$t = 8 \text{ ms}$ square wave	–	6	A
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	junction temperature		–	125	°C
$T_{amb}$	operating ambient temperature		–65	+125	°C

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## PMEG2005EB

**ELECTRICAL CHARACTERISTICS**

$T_{amb} = 25\text{ }^{\circ}\text{C}$ ; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$V_F$	continuous forward voltage	see Fig.2			
		$I_F = 0.1\text{ mA}$	120	180	mV
		$I_F = 1\text{ mA}$	180	240	mV
		$I_F = 10\text{ mA}$	245	290	mV
		$I_F = 100\text{ mA}$	320	380	mV
		$I_F = 500\text{ mA}$	430	480	mV
$I_R$	continuous reverse current	$V_R = 10\text{ V}$ ; see Fig.3; note 1	7	30	$\mu\text{A}$
$C_d$	diode capacitance	$V_R = 1\text{ V}$ ; $f = 1\text{ MHz}$ ; see Fig.4	24	30	pF

**Note**

1. Pulsed test:  $t_p = 300\text{ }\mu\text{s}$ ;  $\delta = 0.02$ .

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\text{ j-a}}$	thermal resistance from junction to ambient	note 1	400	K/W

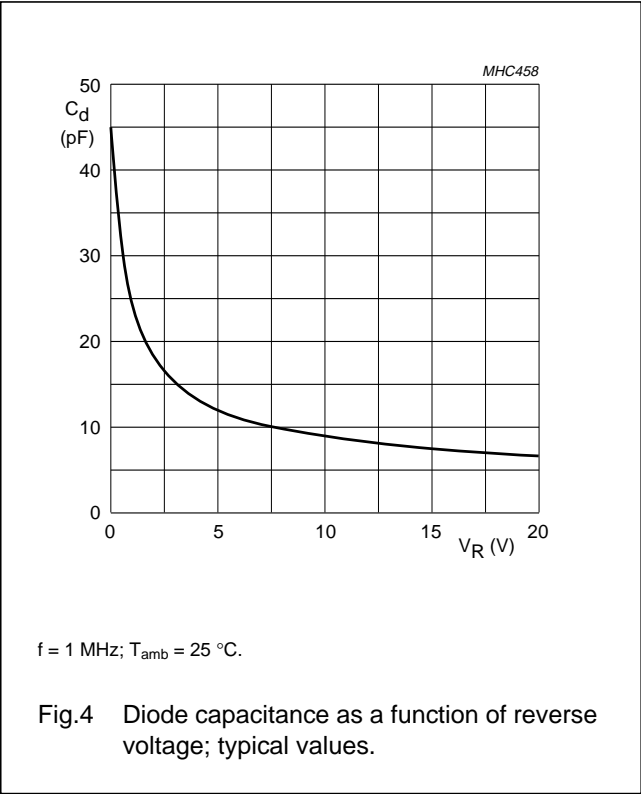
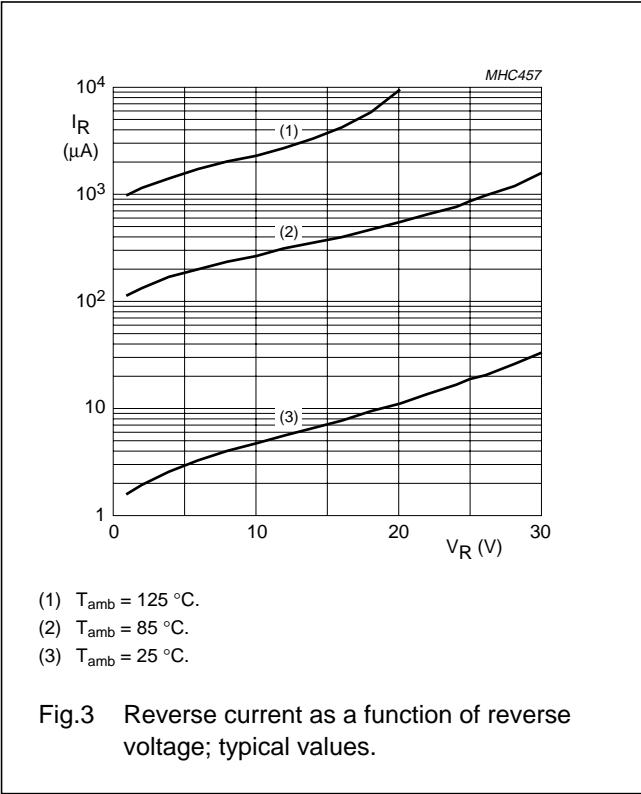
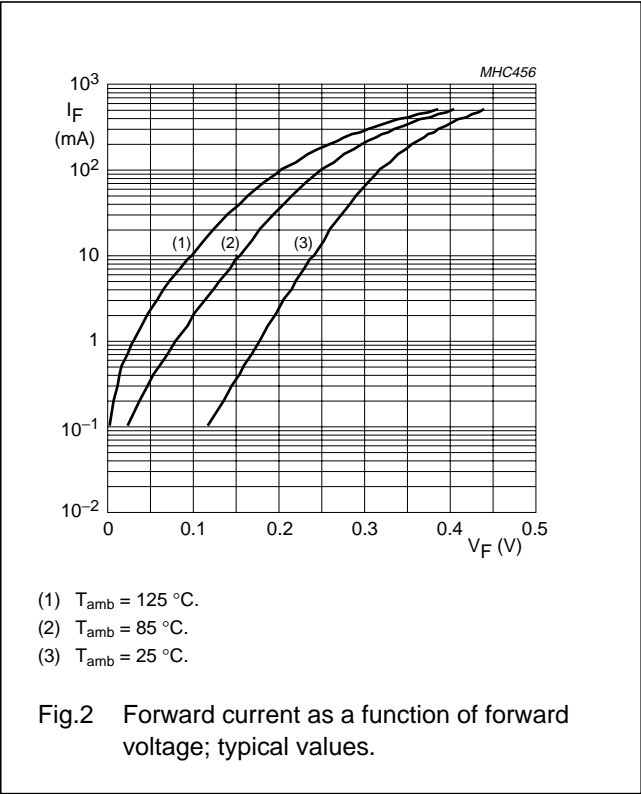
**Note**

1. Refer to SOD523 (SC-79) standard mounting conditions.

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GRAPHICAL DATA



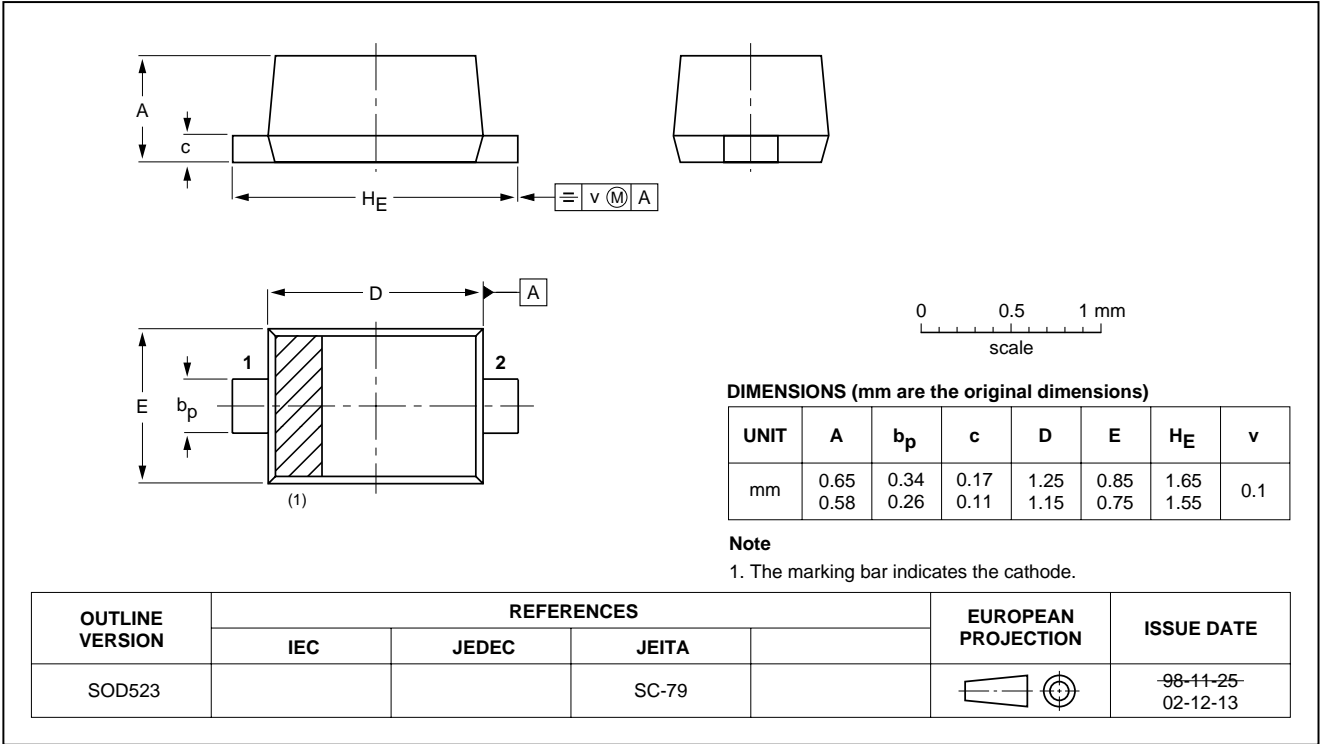
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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD523



Low  $V_F$  MEGA Schottky barrier diode

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## DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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**NOTES**

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